

Xin Chen

List of Publications by Year in descending order

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187
citing authors

#	ARTICLE	IF	CITATIONS
1	Normally-off HEMTs With Regrown p-GaN Gate and Low-Pressure Chemical Vapor Deposition SiN _x Passivation by Using an AlN Pre-Layer. IEEE Electron Device Letters, 2019, 40, 1495-1498.	3.9	50
2	High-Voltage and High-ON/OFF Quasi-Vertical GaN-on-Si Schottky Barrier Diode With Argon-Implanted Termination. IEEE Electron Device Letters, 2021, 42, 473-476.	3.9	37
3	Reverse leakage and breakdown mechanisms of vertical GaN-on-Si Schottky barrier diodes with and without implanted termination. Applied Physics Letters, 2021, 118, .	3.3	26
4	Nitrogen-Implanted Guard Rings for 600-V Quasi-Vertical GaN-on-Si Schottky Barrier Diodes With a BFOM of 0.26 GW/cm ² . IEEE Transactions on Electron Devices, 2021, 68, 5682-5686.	3.0	24
5	Effect of Thermal Cleaning Prior to p-GaN Gate Regrowth for Normally Off High-Electron-Mobility Transistors. ACS Applied Materials & Interfaces, 2019, 11, 21982-21987.	8.0	22
6	Determination of carbon-related trap energy level in (Al)GaN buffers for high electron mobility transistors through a room-temperature approach. Applied Physics Letters, 2020, 117, .	3.3	18
7	Influence of the carrier behaviors in p-GaN gate on the threshold voltage instability in the normally off high electron mobility transistor. Applied Physics Letters, 2021, 119, .	3.3	14
8	Gate Reliability and its Degradation Mechanism in the Normally OFF High-Electron-Mobility Transistors With Regrown p-GaN Gate. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 3715-3724.	5.4	8
9	Improved minority carrier lifetime in p-type GaN by suppressing the non-radiative recombination process. Applied Physics Express, 2022, 15, 075501.	2.4	5
10	Influence of traps on the gate reverse characteristics of normally-off high-electron-mobility transistors with regrown p-GaN gate. Applied Physics Express, 2021, 14, 104005.	2.4	3
11	Influence of Mg doping level at the initial growth stage on the gate reliability of p-GaN gate HEMTs. Journal Physics D: Applied Physics, 2022, 55, 355103.	2.8	3